

# Radiation Hardened 16Mb Asynchronous SRAM SMV512K32



High performance 16Mbit Asynchronous SRAM manufactured with HARDSIL® technology featuring extremely low operational and standby power, latch-up immunity and on-chip EDAC.

## KEY FEATURES

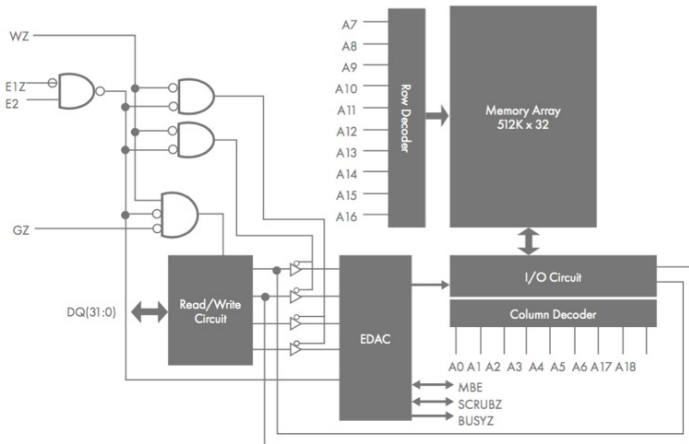
- Manufactured with HARDSIL® technology
- 20nS Read, 13.8nS Write Through maximum access time
- Functionally compatible with commercial 512K x 32 SRAM devices
- Operating voltages
  - Core 1.5V, IO 3.3V
- Built-in Error detection and correction (EDAC) to mitigate soft errors
- Built-in Scrub engine for autonomous correction
- Low standby current < 18mA typical at 125°C
- Die available, part number SMV512K32-DB1FOE
- Packaged devices available from Texas Instruments

## RADIATION HARDENED PERFORMANCE

- TID > 300K rad (Si)
- Soft Error Rate (SER) with EDAC & Scrub enabled: < 5e-17 errors / bit-day
- Latch-up Immunity > LET - 110 MeV-cm<sup>2</sup> / mg (T=125°C)

## APPLICATIONS

- Industrial
- Oil & gas
- Medical
- Aerospace



Description	Part number	Environment	Temperature Range	Package
Radiation-hardened 16Mb Asynchronous SRAM	SMV512K32-DB1FOE	Rad-hard 300K rad (Si)	-55 to 125 °C	Die
Radiation-hardened 16Mb Asynchronous SRAM	SMV512K32HFG (Available from Texas Instruments)	Rad-hard 300K rad (Si)	-55 to 125 °C	76-pin HFG

For more information, contact below or visit our web site at [www.voragotech.com](http://www.voragotech.com)

VORAGO Technologies | 2028 East Ben White Blvd Suite 220, Austin, Texas, 78741 | [info@voragotech.com](mailto:info@voragotech.com)